# BGU7045 1 GHz wideband low-noise amplifier with bypass Rev. 3 — 11 April 2018 Pro

**Product data sheet** 

#### **Product profile** 1

## 1.1 General description

The BGU7045 MMIC is a 3.3 V wideband amplifier with bypass mode. It is designed specifically for high linearity, low-noise applications over a frequency range of 40 MHz to 1 GHz. It is especially suited for Set-Top Box applications.

The LNA is housed in a 6-pin SOT363 plastic SMD package.

#### 1.2 Features and benefits

- Voltage supply of 3.3 V
- · Internally biased
- Programmable between G<sub>p</sub> = 14 dB and bypass
- Flat gain between 40 MHz and 1 GHz
- Noise figure of 2.8 dB
- $\bullet$  High linearity with an IP30 of 29 dBm
- 75  $\Omega$  input and output impedance
- · Power-down during bypass mode
- Bypass mode current consumption < 5 mA
- ESD protection > 2 kV Human Body Model (HBM) and >1.5 kV Charged Device Model (CDM) on all pins

# 1.3 Applications

- Terrestrial and cable Set-Top Boxes (STB)
- Silicon and "Can" tuners
- Personal Video Recorders (PVR) and Digital Video Recorders (DVR)
- · Home networking and in-house signal distribution



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#### 1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb}$  = 25 °C; typical values at  $V_{CC}$  = 3.3 V;  $Z_{S}$  =  $Z_{L}$  = 75  $\Omega$ ;  $R_{bias}$  = 18  $\Omega$ ; 40 MHz  $\leq$   $f_{1}$   $\leq$  1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		3.1	3.3	3.5	V
I <sub>CC(tot)</sub>	total supply current	G <sub>p</sub> = 14 dB mode	[1]	30	34	38	mA
		bypass mode	[1]	-	3	-	mA
T <sub>amb</sub>	ambient temperature			-40	-	+85	°C
NF	noise figure	G <sub>p</sub> = 14 dB mode	[1]	_	2.8	-	dB
		bypass mode	[1]	-	2.5	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	G <sub>p</sub> = 14 dB mode; 1 GHz	[1]	-	13	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	G <sub>p</sub> = 14 dB mode	[1][2]	-	29	-	dBm

# **Pinning information**

Table 2 Pinning

Table 2. Pinning							
Pin	Description		Simplified outline	Graphic symbol			
1	RF_OUT						
2	V <sub>CC</sub>		6 15 14	$\begin{vmatrix} 3 & 2 \\ 1 & 1 \end{vmatrix}$			
3	n.c.			6 — 1			
4	CTRL		H <sub>1</sub> H <sub>2</sub> H <sub>3</sub>				
5	GND		1 <u></u> 1	5 4 sym141			
6	RF_IN						

# **Ordering information**

**Table 3. Ordering information** 

Type number	Package Name	Description	Version
BGU7045	-	plastic surface-mounted package; 6 leads	SOT363

Mode depends on setting of  $V_{CTRL}$ ; see <u>Table 8</u>. The fundamental frequency ( $f_1$ ) is 1000 MHz. The intermodulation product (IM3) is 2 x  $f_2$  -  $f_1$ , where  $f_2$  =  $f_1$  ± 1 MHz. Input

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# **Marking**

Table 4. Marking code

- auto- in maniming code								
Type number	Marking code	Description						
BGU7045	LK*	* = p: made in Hong Kong						
		* = W: made in China						
		* = t: made in Malaysia						

# **Limiting values**

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled		-0.6	3.5	٧
V <sub>CTRL</sub>	voltage on CTRL pin		[1]	0	$V_{CC}$	٧
I <sub>CC(tot)</sub>	total supply current			-	60	mA
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 100 °C	[2]	-	250	mW
Pi	input power	single tone		-	20	dBm
T <sub>stg</sub>	storage temperature			-65	+150	°C
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-40	+85	°C
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM); according to JEDEC standard 22- A114E		2	-	kV
		Charged Device Model (CDM); according to JEDEC standard 22- C101B		1.5	-	kV

 $V_{CTRL}$  must not exceed  $V_{CC};\,I_{CTRL}$  must be limited to 5 mA (maximum).  $T_{sp}$  is the temperature at the solder point of the ground lead.

**Remark:** V<sub>CTRL</sub> must not exceed V<sub>CC</sub>; I<sub>CTRL</sub> must be limited to a maximum of 5 mA.

# Thermal characteristics

Table 6. Thermal characteristics

	abio of filedinal ordinatorion							
Symbol	Parameter	Conditions		Тур	Unit			
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[1]	130	K/W			

[1] Determined by final element method simulation with device mounted on application board and in still air.

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#### **Characteristics** 7

**Table 7. Characteristics** 

 $T_{amb}$  = 25 °C; typical values at  $V_{CC}$  = 3.3 V;  $Z_{S}$  =  $Z_{L}$  = 75  $\Omega$ ;  $R_{bias}$  = 18  $\Omega$ ; 40 MHz  $\leq$   $f_{1}$   $\leq$  1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled		3.1	3.3	3.5	V
I <sub>CC(tot)</sub>	total supply current	G <sub>p</sub> = 14 dB mode	[1]	30	34	38	mA
		bypass mode	[1]	-	3	-	mA
$ s_{21} ^2$	insertion power gain	G <sub>p</sub> = 14 dB mode	[1]	-	14	-	dB
		bypass mode	[1]	-	-2	-	dB
SL <sub>sl</sub>	slope straight line	G <sub>p</sub> = 14 dB mode		-	-1	-	dB
FL	flatness of frequency response	G <sub>p</sub> = 14 dB mode		-	0.2	-	dB
NF	noise figure	G <sub>p</sub> = 14 dB mode	[1]	-	2.8	-	dB
		bypass mode	[1]	-	2.5	-	dB
RLin	input return loss	G <sub>p</sub> = 14 dB mode	[1]	-	20	-	dB
		bypass mode	[1]	-	9	-	dB
RL <sub>out</sub>	output return loss	G <sub>p</sub> = 14 dB mode	[1]	-	12	-	dB
		bypass mode	[1]	-	10	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	G <sub>p</sub> = 14 dB mode; 1 GHz	[1]	-	13	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	G <sub>p</sub> = 14 dB mode	[1][2]	-	29	-	dBm
		bypass mode	[1][2]	-	27	-	dBm
	The state of the s	The state of the s					1

## Table 8. Gain selection (pin CTRL)

-10 °C  $\leq$   $T_{amb} \leq$  +70 °C; recommended power-up condition:  $V_{CTRL}$  = logic 0 or < 0.7 V.

V <sub>CTRL</sub> (V)	Mode
≤ 0.7	bypass
≥ 1.5	G <sub>p</sub> = 14 dB

**Remark:** V<sub>CTRL</sub> must not exceed V<sub>CC</sub>; I<sub>CTRL</sub> must be limited to a maximum of 5 mA.

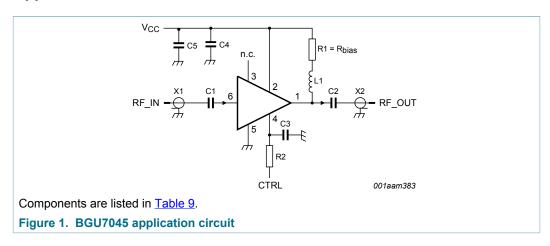
 <sup>[1]</sup> Mode depends on setting of V<sub>CTRL</sub>; see <u>Table 8</u>.
 [2] The fundamental frequency (f<sub>1</sub>) is 1000 MHz. The intermodulation product (IM3) is 2 × f<sub>2</sub> - f<sub>1</sub>, where f<sub>2</sub> = f<sub>1</sub> ± 1 MHz. Input

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# 8 Application information

- Application notes are available on the NXP website.
- Section 8.1 describes the application circuit used for characterisation and datasheet.
- Section 8.2 describes the recommended application circuit.

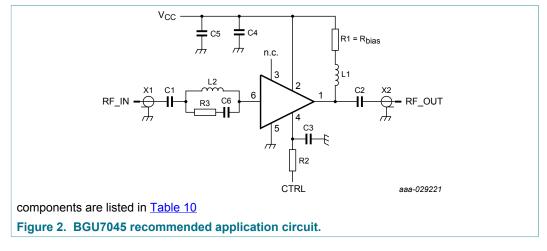
# 8.1 Application circuit



All control and supply lines must be decoupled properly. The decoupling capacitors must be placed as close to the device as possible.

# 8.2 Recommended application circuit

Recommended application circuit to compensate capacitive load influence at RF input.



(Values can be changed depending on the PCB routing) Keep the components (L2, R3, C6) next to the BGU7045 RF input pin.

BGU7045

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# 8.3 Application circuit board layout

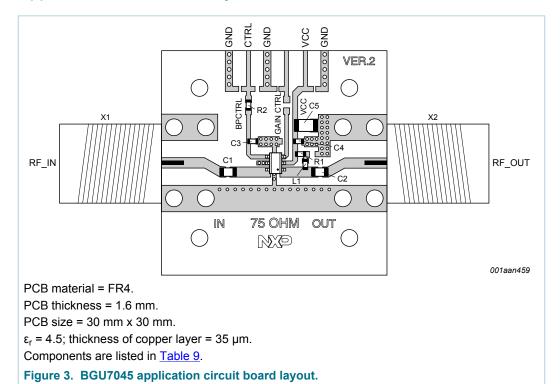


Table 9. List of components

See Figure 1 and Figure 3.

Component	Description	Value		Remarks	Function
C1, C2	capacitor	10 nF			DC blocking
C3, C4	capacitor	10 nF			decoupling
C5	capacitor	10 µF			decoupling
L1	chip ferrite bead	1.5 kΩ	[1]	Murata BLM18HE152SN1DF	RF choke
R1	resistor	18 Ω	[1]	R <sub>bias</sub>	bias setting
R2	resistor	1.8 kΩ			current limiting
X1, X2	connector	75 Ω		F-connector, edge mount PCB reflow type, Bomar 861V509ER6	input/output

[1] L1 and R1 must have a power rating of 0.1 W or higher.

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Table 10. List of components for recommended application circuit See  $\underline{\text{Figure 2}}$ .

Component	Description	Value		Remarks	Function
C1, C2	capacitor	10 nF			DC blocking
C3, C4	capacitor	10 nF			decoupling
C5	capacitor	10 μF			decoupling
C6	capacitor	0.5 pF		Murata GRM1555C1HR50BA01	value depends on layout
L1	chip ferrite bead	1.5 kΩ	[1]	Murata BLM18HE152SN1DF	RF choke
L2	inductor	2.7 nH		Murata LQG11A2N7	value depends on layout
R1	resistor	18 Ω	[1]	R <sub>bias</sub>	bias setting
R2	resistor	1.8 kΩ			current limiting
R3	resistor	47 Ω			
X1, X2	connector	75 Ω		F-connector, edge mount PCB reflow type, Bomar 861V509ER6	input/output

<sup>[1]</sup> L1 and R1 must have a power rating of 0.1 W or higher.

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# 9 Package outline

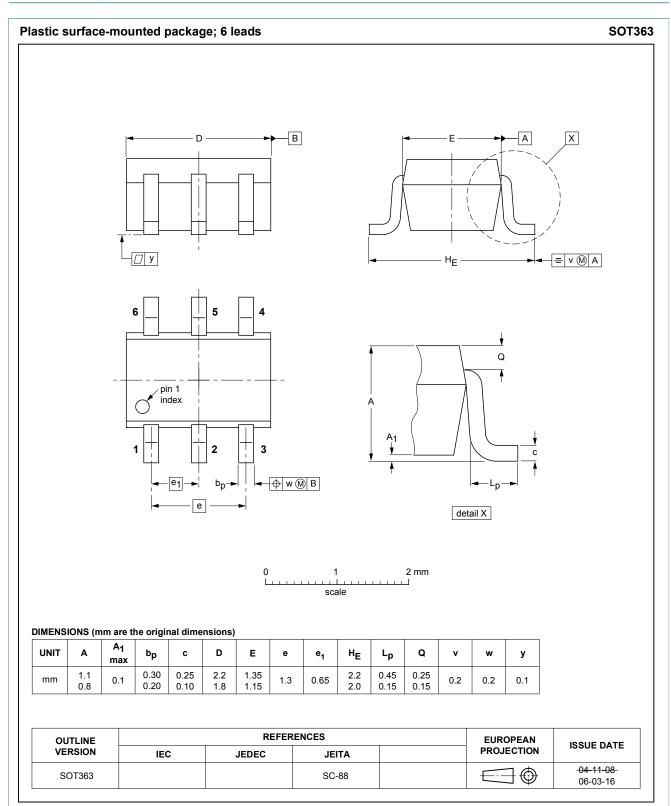


Figure 4. Package outline SOT363

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# 10 Abbreviations

Table 11. Abbreviations

Acronym	Description
AC	Alternating Current
DC	Direct Current
ESD	ElectroStatic Discharge
LNA	Low-Noise Amplifier
MMIC	Monolithic Microwave Integrated Circuit
PCB	Printed-Circuit Board
RF	Radio Frequency
SMD	Surface-Mounted Device

# 11 Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
BGU7045 v.3	20180411	product data sheet	-	BGU7045 v.2				
Modification	added recommend	added recommended application circuit with components table						
BGU7045 v.2	20140526	product data sheet	-	BGU7045 v.1				
Modifications:	difications:  • <u>Table 6 on page 3</u> : The information in this table has been updated.							
BGU7045 v.1	20120203	product data sheet	-	-				

#### 1 GHz wideband low-noise amplifier with bypass

# 12 Legal information

# 12.1 Data sheet status

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